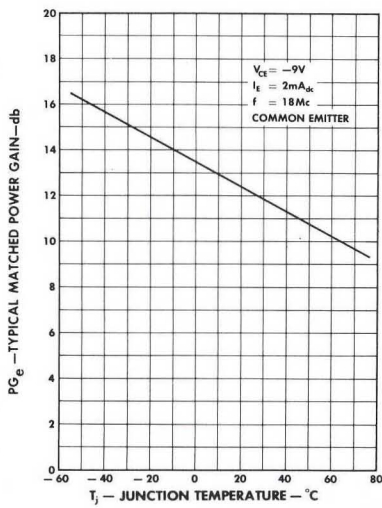
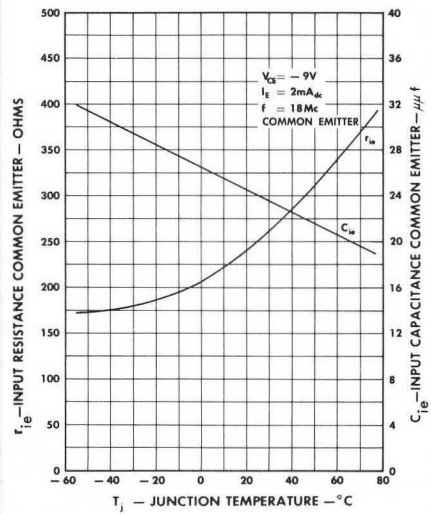


TYPE 2N248

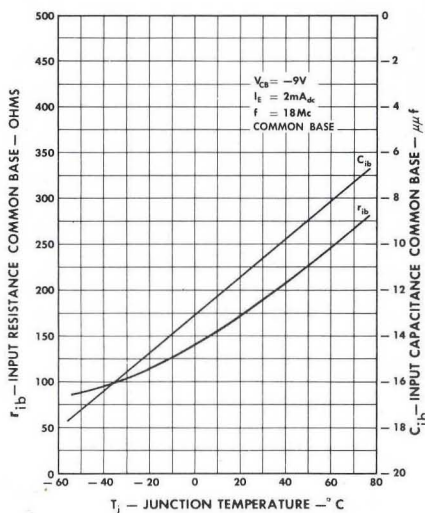
TYPICAL CHARACTERISTICS



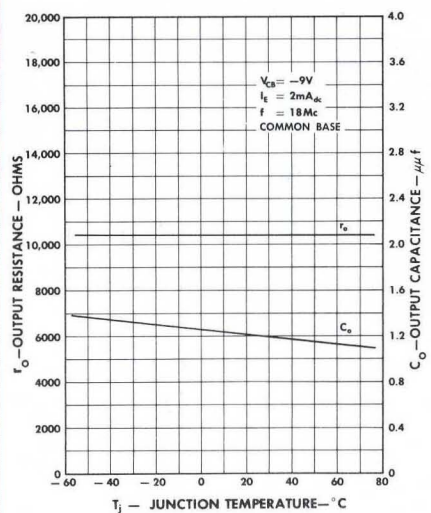
TYPICAL MATCHED POWER GAIN VS. JUNCTION TEMPERATURE



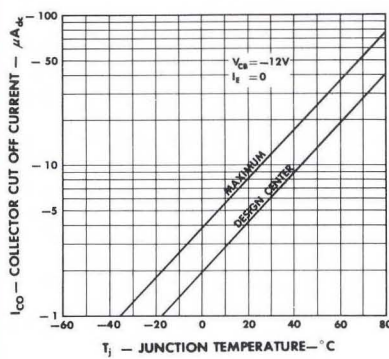
C_{ie} AND r_{ie} VS. JUNCTION TEMPERATURE



C_{ib} AND r_{ib} VS. JUNCTION TEMPERATURE



C_o AND r_o VS. JUNCTION TEMPERATURE

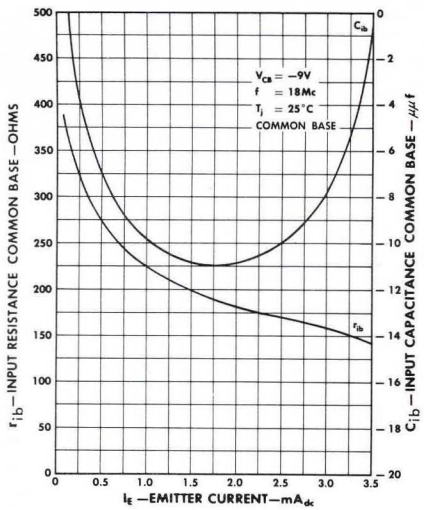


COLLECTOR CUTOFF CURRENT VS. JUNCTION TEMPERATURE

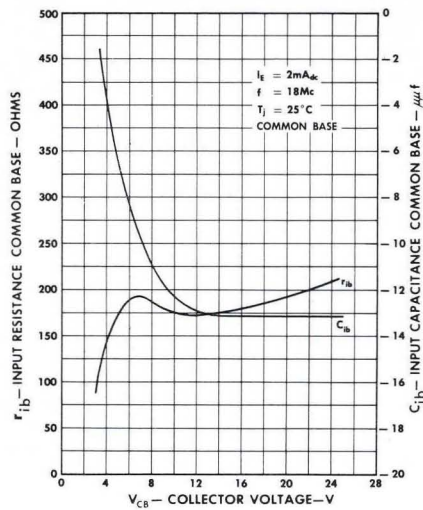
TEXAS INSTRUMENTS
INCORPORATED

SEMICONDUCTOR COMPONENTS DIVISION
POST OFFICE BOX 312 • 13500 N. CENTRAL EXPRESSWAY
DALLAS, TEXAS

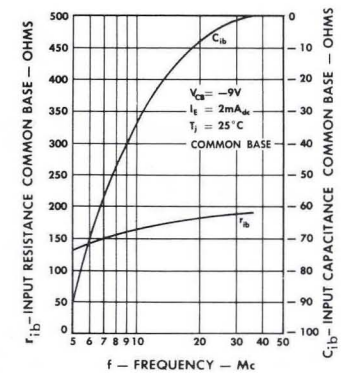
TEXAS INSTRUMENTS RESERVES THE RIGHT TO MAKE CHANGES AT ANY TIME IN ORDER TO IMPROVE DESIGN.



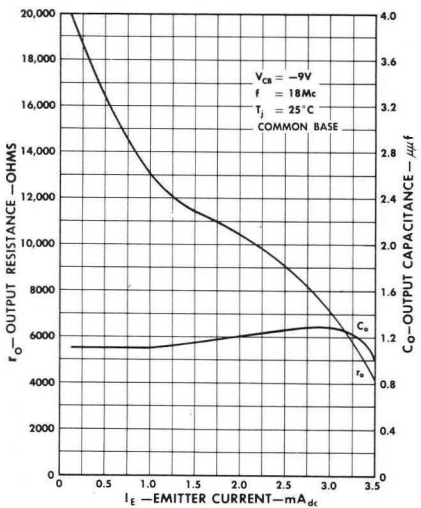
C_{ib} AND r_{ib} VS. EMITTER CURRENT



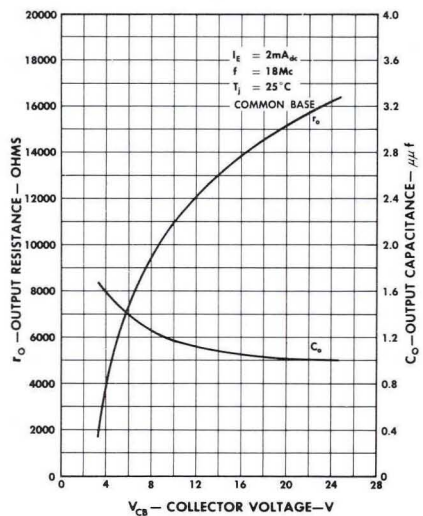
C_{ib} AND r_{ib} VS. COLLECTOR VOLTAGE



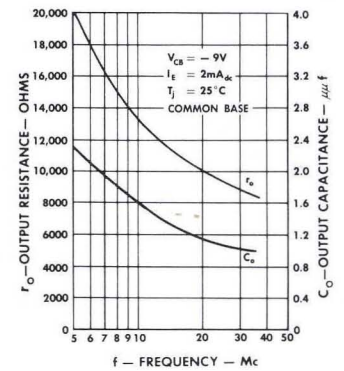
C_{ib} AND r_{ib} VS. FREQUENCY



C_o AND r_o VS. EMITTER CURRENT



C_o AND r_o VS. COLLECTOR VOLTAGE



C_o AND r_o VS. FREQUENCY

TEXAS INSTRUMENTS
INCORPORATED

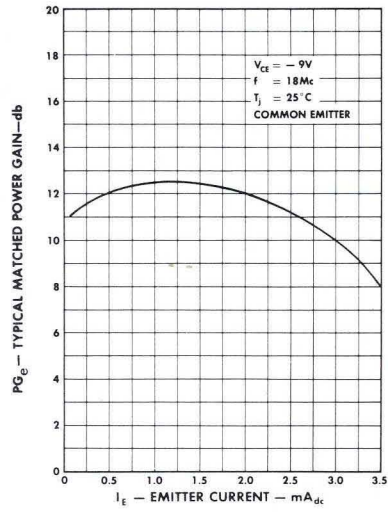
SEMICONDUCTOR COMPONENTS DIVISION
POST OFFICE BOX 312 • 13500 N. CENTRAL EXPRESSWAY
DALLAS, TEXAS



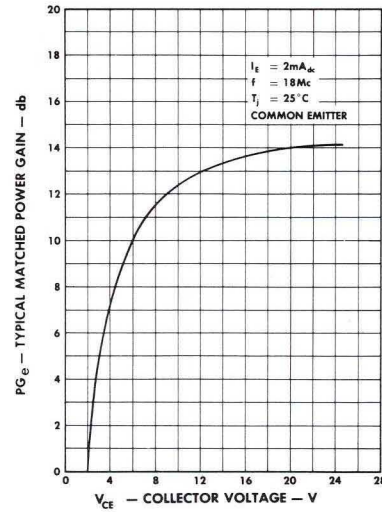
SEMICONDUCTOR-COMPONENTS DIVISION

TYPE 2N248

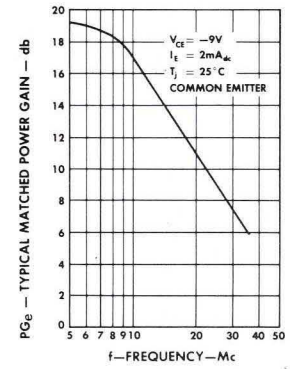
TYPICAL CHARACTERISTICS



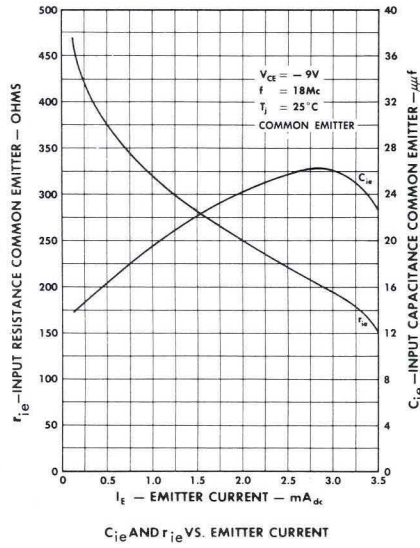
TYPICAL MATCHED POWER GAIN VS. EMITTER CURRENT



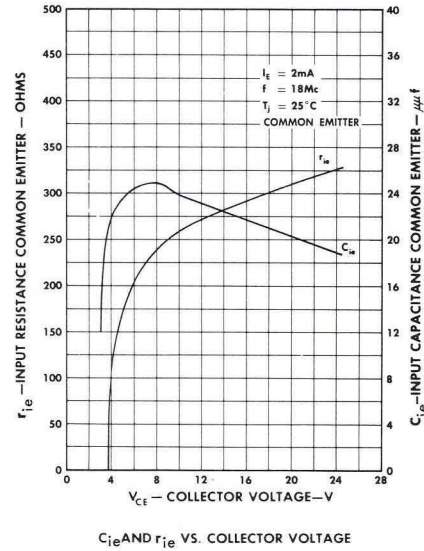
TYPICAL MATCHED POWER GAIN VS. COLLECTOR VOLTAGE



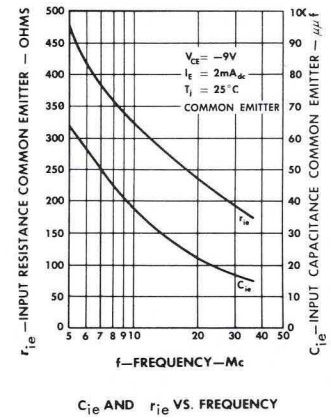
TYPICAL MATCHED POWER GAIN VS. FREQUENCY



C_{ie} AND r_{ie} VS. EMITTER CURRENT



C_{ie} AND r_{ie} VS. COLLECTOR VOLTAGE



C_{ie} AND r_{ie} VS. FREQUENCY